



TO-92MOD Plastic-Encapsulate Transistors

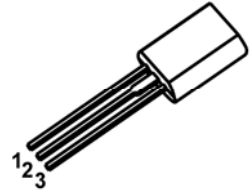
2SC2383 TRANSISTOR (NPN)

TO-92MOD

FEATURE

- High Voltage: $V_{CEO}=160V$
- Large Continuous Collector Current Capability
- Complementary to 2SA1013

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



MAXIMUM RATINGS ($T_a=25\text{ }^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}C$

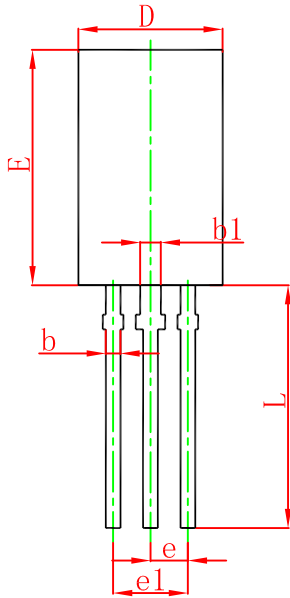
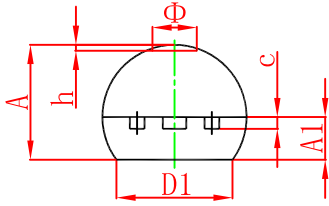
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=100\mu A, I_E=0$	160		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=10mA, I_B=0$	160		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=10\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=150V, I_E=0$		1	μA
Collector cut-off current	I_{CER}	$V_{CB}=150V, R_{EB}=10M\Omega$		10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$		1	μA
DC current gain	h_{FE1}	$V_{CE}=5V, I_C=200mA$	60	320	
	h_{FE2}	$V_{CE}=5V, I_C=10mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		1	V
Base-emitter voltage	V_{BE}	$I_C=5mA, V_{CE}=5V$		0.75	V
Transition frequency	f_T	$V_{CE}=5V, I_C=200mA$	20		MHz

CLASSIFICATION OF h_{FE1}

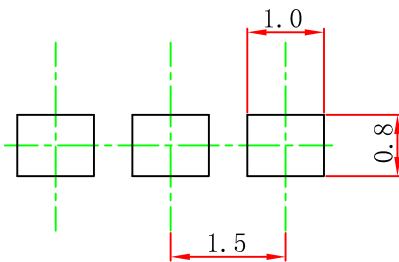
Rank	R	O	Y
Range	60-120	100-200	160-320

TO-92MOD Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.800	5.000	0.189	0.197
A1	1.730	2.030	0.068	0.080
b	0.440	0.600	0.017	0.024
b1	0.940	1.100	0.037	0.043
c	0.350	0.450	0.014	0.018
D	5.900	6.100	0.232	0.240
D1	4.000		0.157	
E	8.500	8.700	0.335	0.343
e	1.500 TYP.		0.059 TYP.	
e1	2.900	3.100	0.114	0.122
L	13.800	14.200	0.543	0.559
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92MOD Suggested Pad Layout



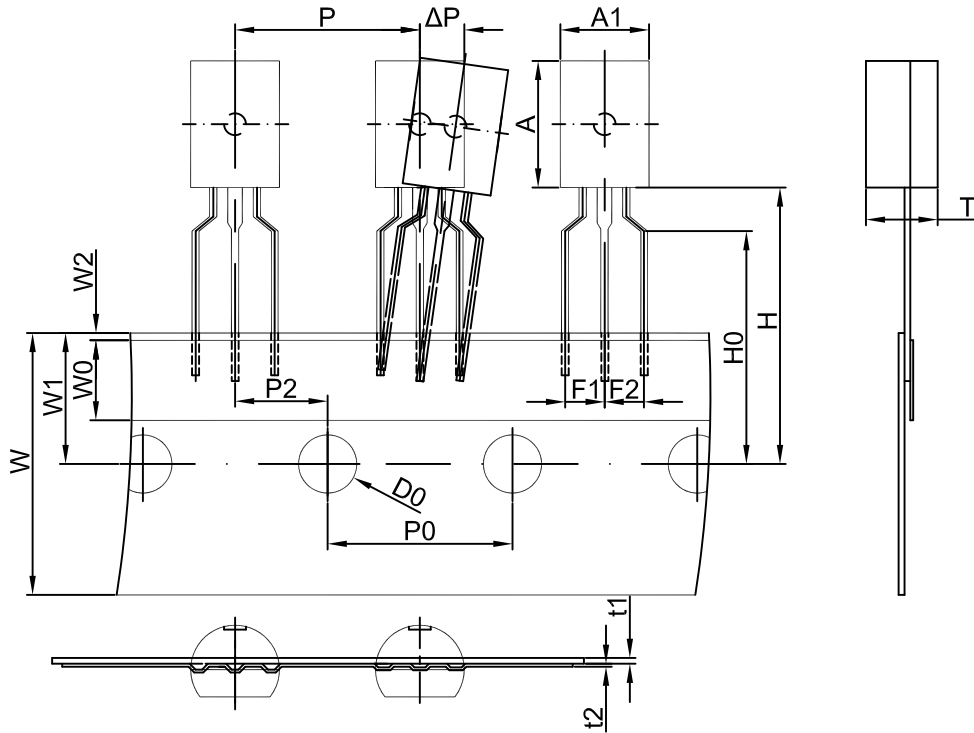
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

NOTICE

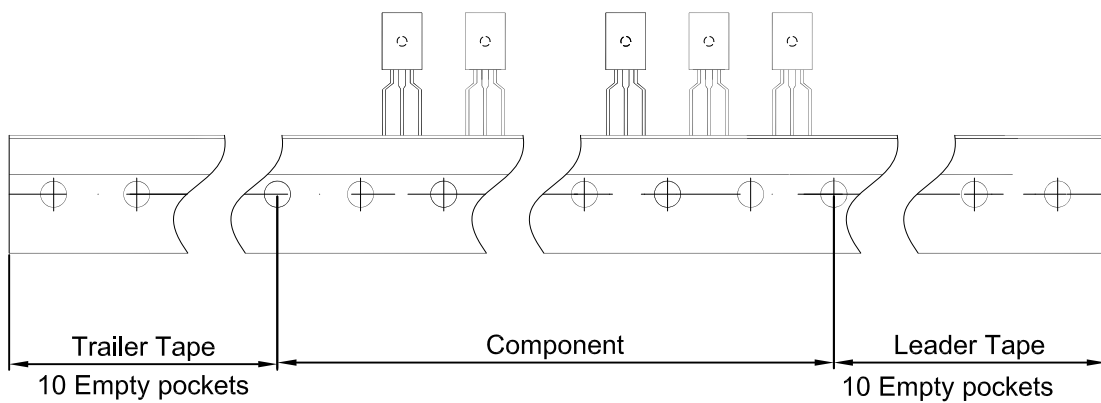
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TO-92MOD PACKAGE TAPEING DIMENSION



Dimensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
6.0	8.6	4.9	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92MOD	2000 pcs	333×245×43	20,000 pcs	573×404×266

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